



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re application of:

Masato TAKITA, et al.

Art Unit: 2823

Serial No.: 09/046,671

Examiner: J. Maldonado

Filed: March 24, 1998

Docket No.: 108077-08003

For: SEMICONDUCTOR DEVICE AND METHOD FOR FABRICATING THE
SAME

AMENDMENT UNDER 37 CFR §1.111

Commissioner for Patents
Washington, D.C. 20231

February 4, 2003

Dear Sir:

In response to the Office Action dated October 4, 2002, the period for reply having been dully extended until February 4, 2003, by the attached Petition for Extension of Time, please reconsider the above-identified application amended as follows:

IN THE CLAIMS:

Please amend claim 1 as follows:

1. (Four times amended) A semiconductor device comprising:
a lightly doped semiconductor substrate of a first conduction type;
a buried semiconductor layer of a second conduction type formed in a first region of the semiconductor substrate, spaced from a surface of the semiconductor substrate;

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